Inventor:

Eugene P. Marsh

Title:

Platinum-containing Integrated Circuits and Capacitor

Constructions

Assignee:

Micron Technology, Inc.

## INFORMATION DISCLOSURE STATEMENT PURSUANT TO 37 C.F.R. §§1.56, 1.97 AND 1.98

In compliance with 37 C.F.R. §§1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449.

The listed references were cited by, or submitted to, the Office in the parent, co-pending application of the above-identified application. The above-identified application is a continuation of co-pending application Serial No. 09/421,625 filed October 19, 1999. Such prior disclosure is sufficient for the above-identified application as far as copies of the references are concerned. 37 C.F.R. §1.98(d) and MPEP §609(2). No admission is made regarding whether all the submitted references are prior art.

Citation of these references is respectfully requested.

Respectfully submitted,

Dated:

8/13/03

Attorney:

David G. Latwesen, Ph.D.

Reg. #38,533

WELLS ST. JOHN P.S.

Form PTO-1449					J.S. DEPARTMENT OF COMMERCE ATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO MI22-2382		PRIORITY SERIAL NO. Filed Herewith				
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						PRIORITY FILING DATE 10/19/99			PRIORITY GROUP Unknown			
					U.S. PATENT DOCUMENTS							
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	AA	4,341	,662	7/82	Pfefferle							
	AB	4,431	,750	2/84	McGinnis et al.							
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	AH	4,719	,442	1/88	Bohara et al.							
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	AI	9-082	2666									
	AJ 0415751 A1			Japan EPO								
				OTHER REFER	RENCES (including Author, Title, Date, I	Pertinent Pages, Etc.)	-					
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[		Ferroelectric Bottom Electrodes"; J. Electrochem. Soc., Vol. 144, No. 8, August 1997; pp. 2848-2854										
	AL	M. Ino et al.; "Rugged surface polycrystalline silicon film deposition and its application in a stacked dynamic random access										
		memory capacitor electrode"; J. Vac. Sci. Technol. B 14(2), March/April 1996; pp. 751-756										
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	AA 5,639,685				Zahurak et al.									
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	AB	6,033	3,953	3/00	Aoki et al.								
	AC	5,990	0,559	11/99	Marsh								
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	Al	5,635	5,420	6/97	Nishioka								
	AJ												
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	AL	JP 80	017939	6/3/03	Japan								
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